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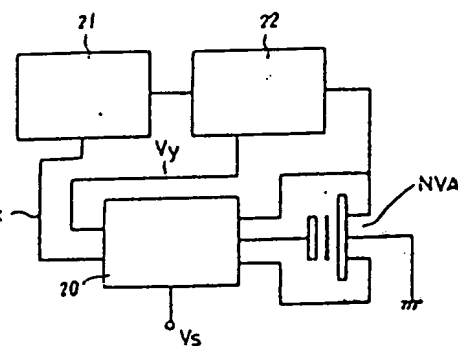
G11C27/00 F

## (54) WRITE-IN CIRCUIT FOR NON-VOLATILE ANALOG MEMORY

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**PURPOSE:** To decrease the time required for write of an analog signal by comparing a threshold voltage of an analog memory with a reference voltage and generating a write-in pulse with a peak value in response to the magnitude of the difference.

**CONSTITUTION:** When a difference between a threshold voltage of a non-volatile analog memory NVAM and a reference voltage  $V_s$  detected at a threshold value detecting circuit 20 becomes greater, a voltage outputted from a voltage control circuit 21 is quickly increased and the peak value of write-in pulse generated from a write-in pulse generating circuit 22 is quickly increased by the increase. As a result, the threshold voltage of the NVAM is rapidly closed to the objective value. On the other hand, when the threshold voltage of the NVAM closes to a desired value and the difference with the voltage  $V_s$  becomes smaller, the increment of the write-in pulse is decreased, allowing to adjust the threshold value of the NVAM minutely. When the both are coincident, the circuit 20 gives an inhibiting signal  $V_y$  to the circuit 22 to complete the write-in operation.



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P. 171